

Erratum: "MoS_{2-x}O_x solid solutions in thin films produced by rf-sputter-deposition"

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After this article was published in the January issue of *Journal of Materials Research*, the author noticed that the binding energy axes in Fig. 1 were labeled incorrectly. All spectra in this figure, i.e., Mo 3d, S 2p,

and O 1s core level spectra for both fresh and annealed films, should be shifted by exactly 2.0 eV to lower binding energy. The corrected figure is shown below.

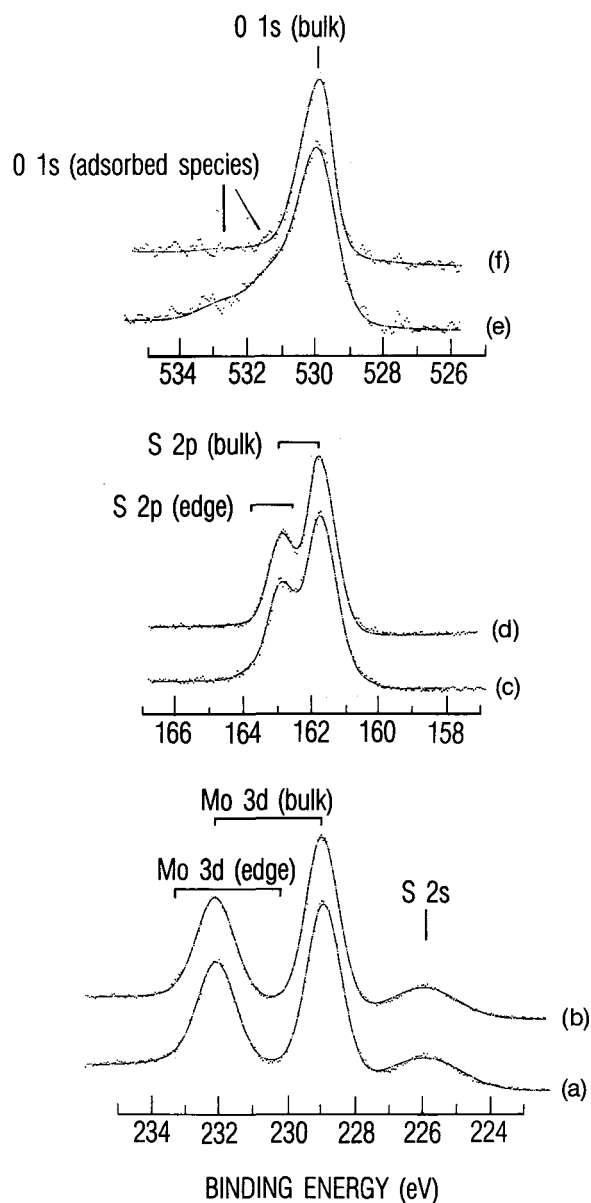


FIG. 1. X-ray photoelectron spectra of an rf-sputter-deposited MoS₂ film deposited on a substrate that was at 525 K (i.e., the HT film). Shown are spectra that were taken before and after annealing to 875 K for the (a, b) Mo 3d; (c, d) S 2p; and (e, f) O 1s core levels. Binding energies are relative to the Au 4f_{7/2} core level at 84.0 eV.